



FEATURES

Dimensions are in inch [metric] units.

- Ideal for electron detection
- Circular active area
- 100% internal QE

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C (PER ELEMENT)

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Active Area			15		mm ²
Responsivity, \mathcal{R}	(see graphs on the next page)	0.07	0.08	0.09	A/W
Shunt Resistance, R_{sH}	$V_R = \pm 10mV$	10			MOhms
Reverse Breakdown Voltage, V_R	$I_R = 1\mu A$	5			Volts
Capacitance, C	$V_R = 0V$		1.5		nF
Rise Time	$V_R = 2V, R_L = 50\Omega$			2	usec

THERMAL PARAMETERS

STORAGE AND OPERATING TEMPERATURE RANGE	
Ambient ¹	-10° TO 40°C ¹
Nitrogen or Vacuum	-20°C TO 80°C
Maximum Junction Temperature	70°C
Lead soldering temperature ²	260°C

¹Temperatures exceeding these parameters may create oxide growth on the active area. Over time responsivity to low energy radiation and wavelengths below 150nm will be compromised.

²0.080" from case for 10 seconds.

Shipped with temporary cover to protect photodiode and wire bond.
Review Opto Diode "Handling Precautions for IRD Detectors" prior to removing cover.



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